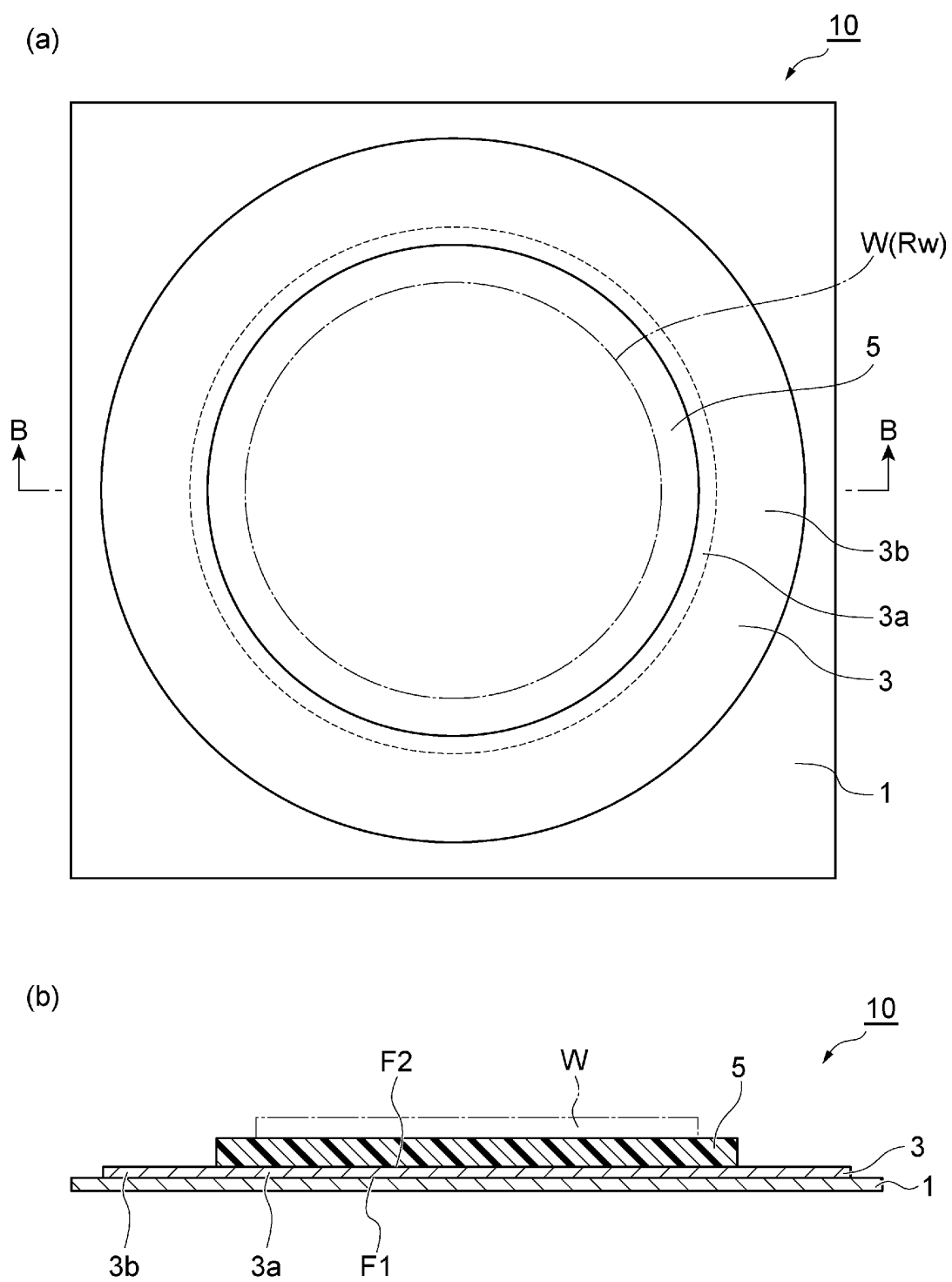
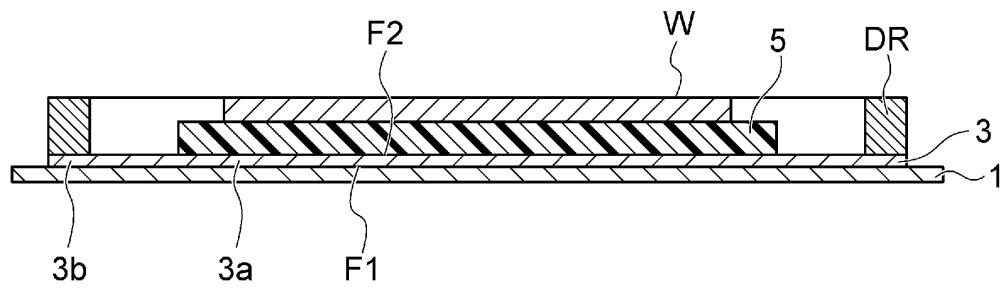


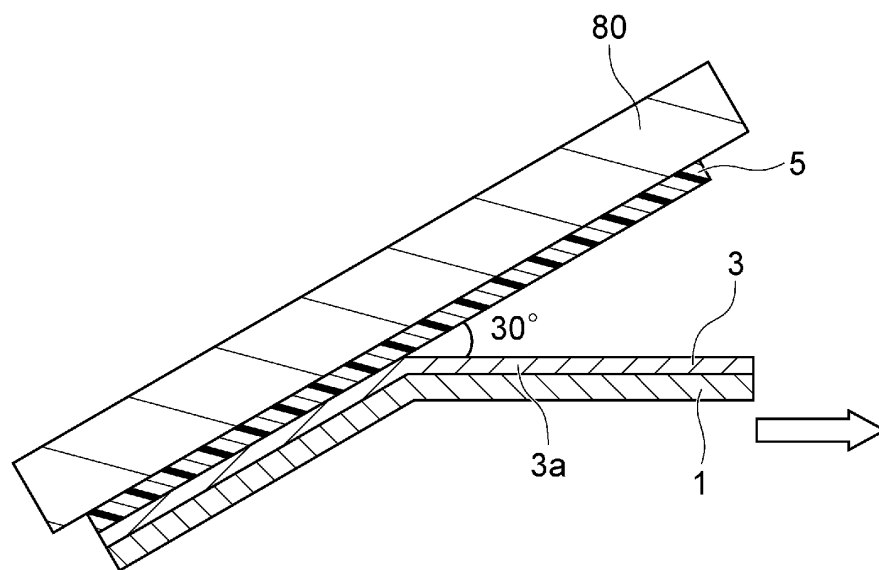
[図1]



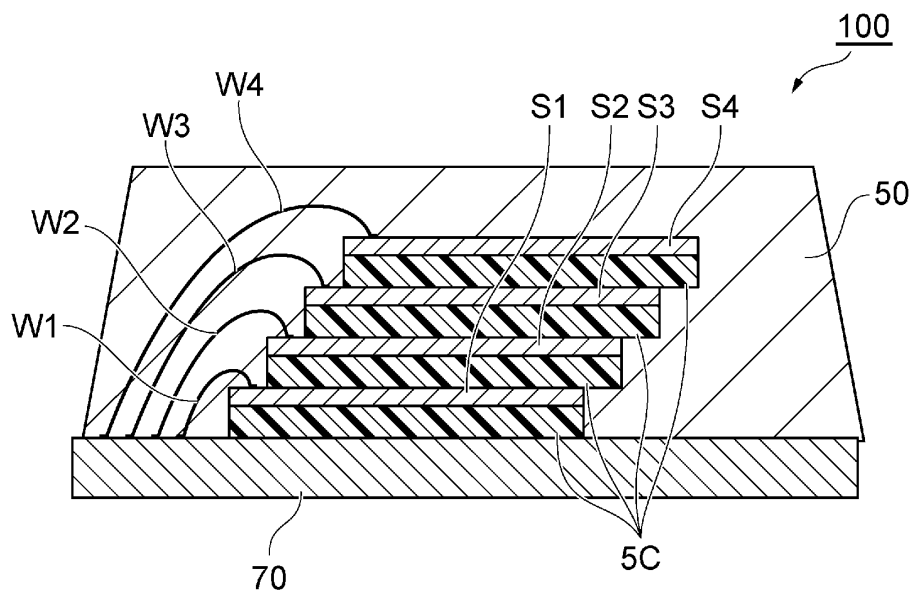
[図2]



[図3]

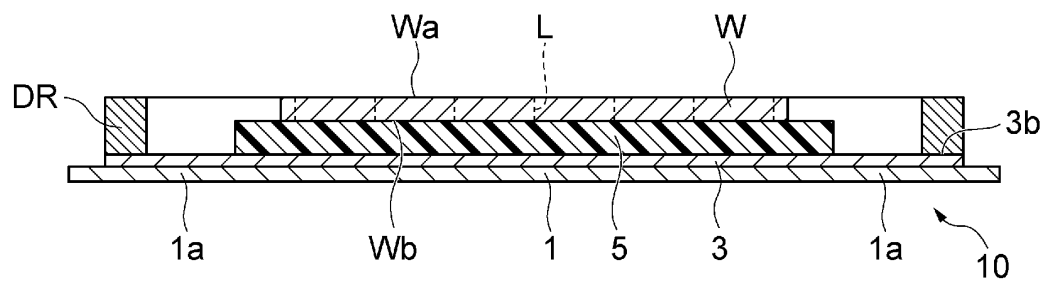


[図4]



[図5]

(a)



(b)

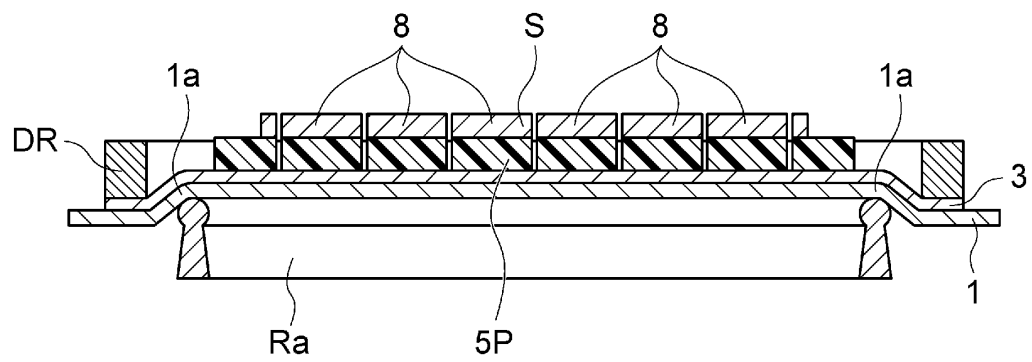
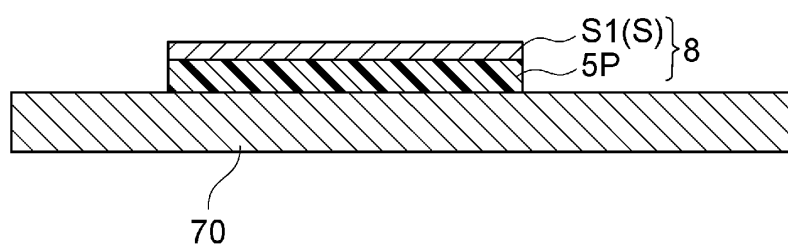


Figure 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 1 with a thin layer 3 on its top surface. A series of rectangular blocks 8 are formed on the surface of layer 3. Each block 8 contains a central layer 5P and side layers S. A layer 42 is located beneath the blocks. A structure 44 is positioned above one of the blocks, and a layer DR is on the left side.

[図7]

(a)



(b)

